



电子元器件系列(中国.厦门) China.Xiamen
www.rf-china.com RF-Micom co.,Ltd

Email:sales@rf-china.com

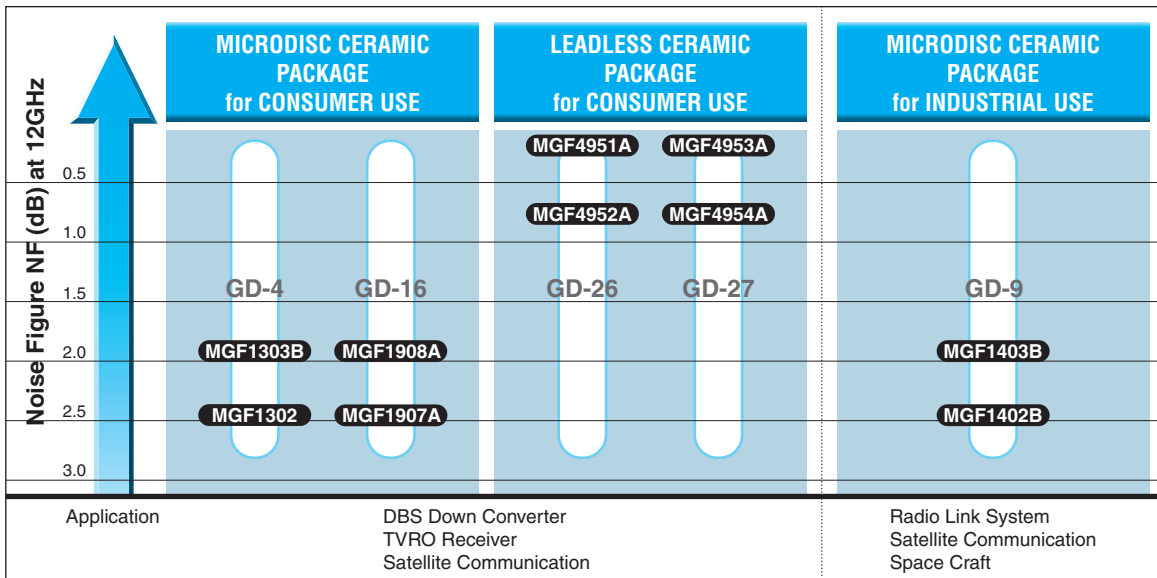
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MITSUBISHI GaAs devices: The best solution for realizing the information era.

Communication networks, such as high speed Internet, video-on-demand and high-speed data communication, are developing rapidly.

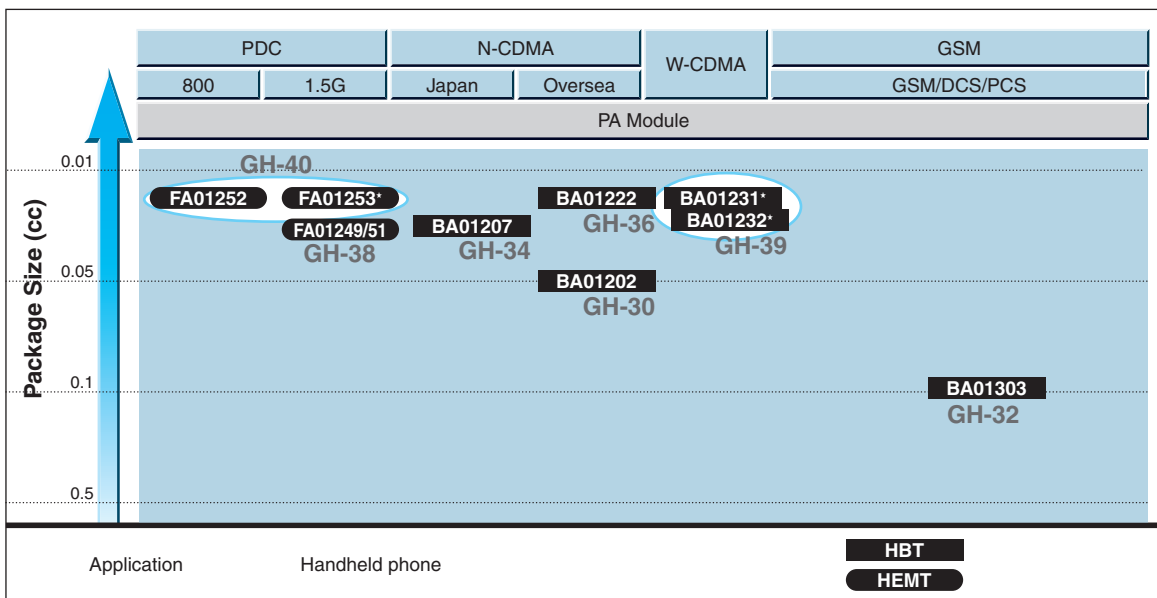
We are ready to offer the best solution to the systems for realizing the information era by providing a variety of GaAs products designed for satellite communication systems to base stations and cellular handset applications.

GaAs FET SERIES FOR MICROWAVE-BAND LOW-NOISE AMPLIFIERS



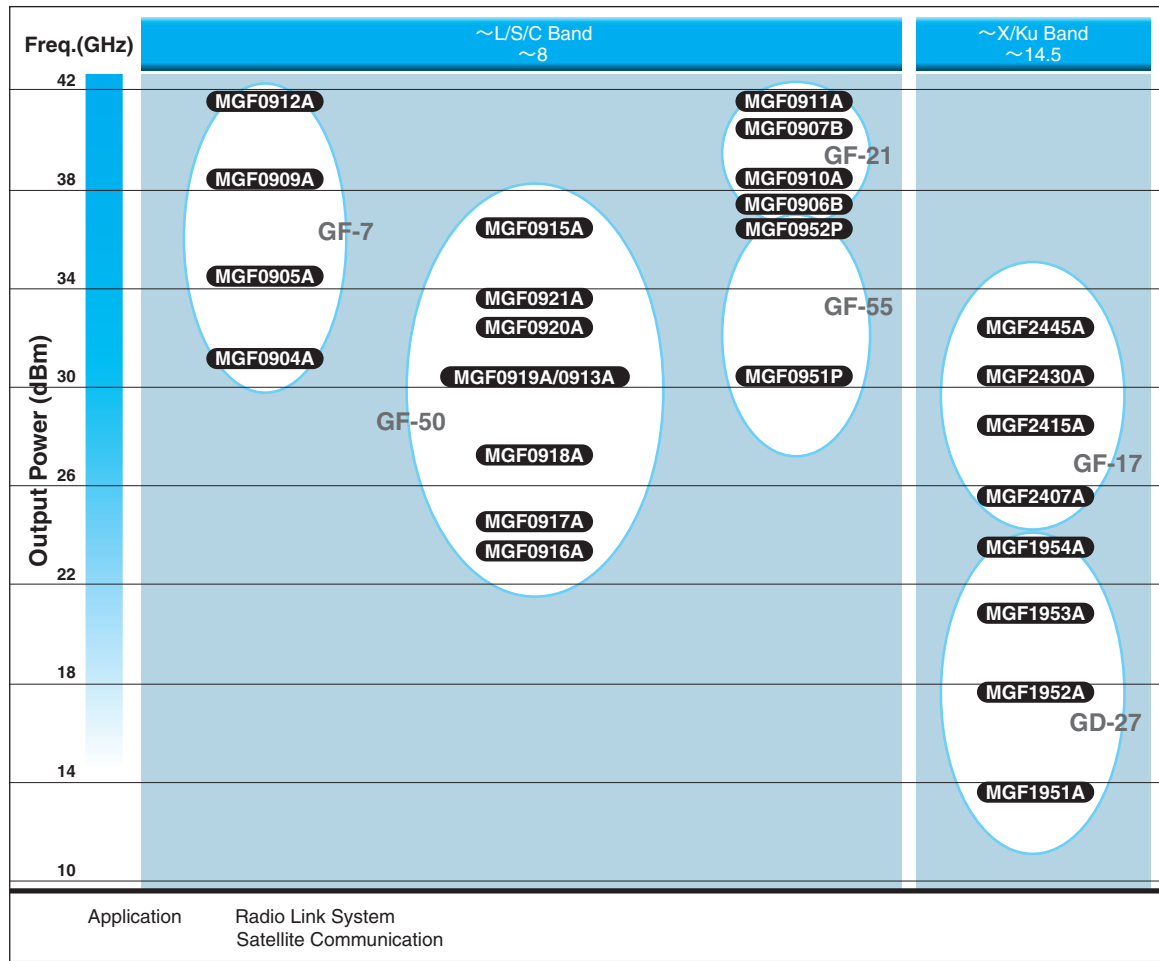
Note : MGF4xxx=HEMT MGF1xxx=MES FET

GaAs HYBRID IC&MMIC

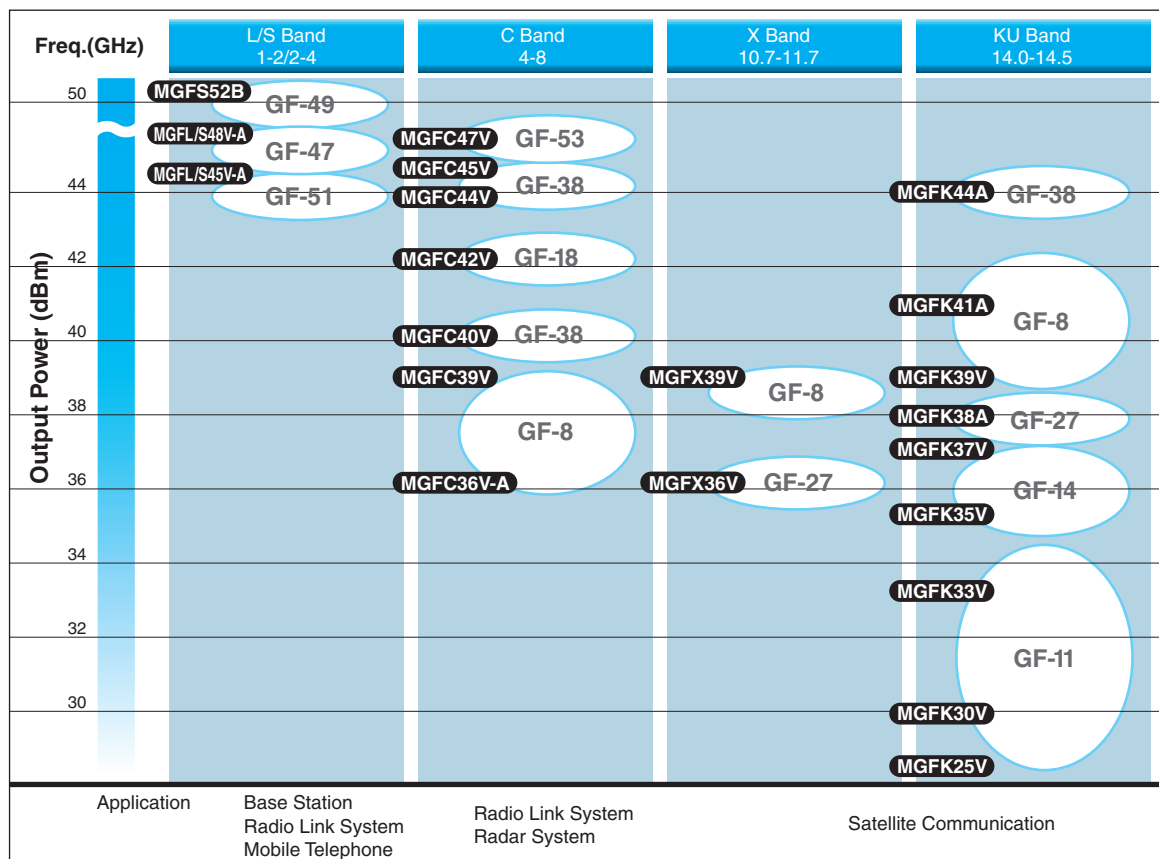


* : New product

GaAs FET FOR HIGH POWER DISCRETE



INTERNALLY MATCHED GaAs FET SERIES FOR MICROWAVE-BAND HIGH POWER AMPLIFIERS



GaAs FET SERIES FOR MICROWAVE- BAND LOW-NOISE AMPLIFIERS

Type Number	Noise Figure(dB)		Associated Gain(dB)		Frequency(GHz)	Drain-Source Voltage(V)	Drain Current(mA)
	Typ.	Max.	Min.	Typ.			
MGF1302	2.7	-	-	9	12	3	10
MGF1303B	2	-	-	10.5	12	3	10
MGF1402B	3	-	-	8	12	3	10
MGF1403B	1.8	-	-	10.5	12	3	10
MGF1907A	2.7	-	-	9	12	3	10
MGF1908A	2	-	-	10.5	12	3	10
MGF4951A	0.40	0.50	11.0	12.0	12	2	10
MGF4952A	0.60	0.80	11.0	12.0	12	2	10
MGF4953A	0.40	0.50	12.0	13.0	12	2	10
MGF4954A	0.60	0.80	12.0	13.0	12	2	10
MGF4955A*	0.40	0.50	11.0	12.0	12	2	7.5
MGF4957A*	0.40	0.50	12.0	13.0	12	2	7.5
MGF4931AM*	0.60	0.80	10.0	11.5	12	2	7.5

Ta=25°C

* : New product

GaAs FET SERIES FOR MICROWAVE- BAND HIGH-POWER AMPLIFIERS(Discrete Devices)

Type Number	Output Power at 1dB Gain Compression(dBm)		Output Power (dBm)	Linear Power Gain(dB)	3rd Order IM Distortion(dBc)		Power Added Efficiency(%)	Frequency (GHz)	Drain-Source Voltage(V)	Drain Current (A)	Thermal Resistance (°C/W)	
	Min.	Typ.			Min.	Typ.					Typ.	Max.
MGF0904A	-	-	26	11	-	-	40	1.65	8	0.2	-	-
MGF0905A	-	-	33	7	-	-	40	1.65	8	0.8	-	-
MGF0906B	35.5	37	-	10	-	-	40	2.3	10	1.2	-	6.5
MGF0907B	38.5	40	-	8	-	-	37	2.3	10	2.4	-	4
MGF0909A	37	38	-	10	-	-	45	2.3	10	1.3	-	-
MGF0910A	37	38	-	10	-	-	37	2.3	10	1.3	-	6
MGF0911A	40	41	-	10	-	-	40	2.3	10	2.6	-	4.5
MGF0912A	-	-	40.5	9.5	-	-	38	1.9	10	2.6	2.3	3
MGF0913A	-	-	29.5	11	-	-	48	1.9	10	0.2	20	30
MGF0915A	-	-	35	13	-	-	50	1.9	10	0.8	5	8
MGF0916A	-	-	21	17	-	-	30	1.9	6	0.1	20	30
MGF0917A	-	-	23	19	-	-	38	1.9	10	0.075	55	75
MGF0918A	-	-	25	18	-	-	45	1.9	10	0.15	35	50
MGF0919A	-	-	28	17	-	-	37	1.9	10	0.3	17	25
MGF0920A	-	-	30	16	-	-	45	1.9	10	0.4	13	18
MGF0921A	-	-	31	15	-	-	40	1.9	10	0.5	11	15
MGF0951P*	29.5	31	-	11	-	-42	50	2.15	10	0.2	20	25
MGF0952P**	35	36.5	-	11	-	-42	50	2.15	10	0.7	5	6
MGF1601B	20.8	21.8	-	6	-	-	-	8	6	0.1	-	125
MGF1801B	21.8	23	-	7	-	-	-	8	6	0.1	-	125
MGF1801BT	21.8	23	-	7	-	-	-	8	6	0.1	-	125
MGF1951A	11	13	-	7	-	-	-	12	3	0.03	-	-
MGF1952A	15	17	-	5	-	-	-	12	3	0.06	-	-
MGF1953A	18	20	-	4	-	-	-	12	4	0.1	-	-
MGF1954A	21	23	-	3	-	-	-	12	6	0.1	-	-
MGF2407A	23	24.5	-	7	-	-	30	14.5	10	0.075	-	100
MGF2415A	26	27.5	-	6.5	-	-	29	14.5	10	0.15	-	60
MGF2430A	29	30.5	-	5.5	-	-	27	14.5	10	0.3	-	30
MGF2445A	31	32	-	5.5	-	-	20	12	10	0.45	-	15
MGF4851A	12	14.5	-	9	-	-	-	12	2.5	0.025	-	-

Ta=25°C

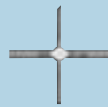
* : New product ** : Under development

INTERNALLY MATCHED GaAs FET SERIES FOR L/S BAND HIGH POWER AMPLIFIERS

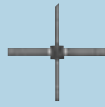
Type Number	Output Power at 1dB Gain Compression(dBm)		Output Power (dBm)	Linear Power Gain(dB)	3rd Order IM Distortion(dBc)		Power Added Efficiency(%)	Frequency (GHz)	Drain-Source Voltage(V)	Drain Current (A)	Thermal Resistance (°C/W)	
	Min.	Typ.			Min.	Typ.					Typ.	Max.
MGFC36V3436	35	37	-	11	-42	-45	32	3.4~3.6	10	1.2	5	6
MGFC39V3436	38	39.5	-	10	-42	-45	32	3.4~3.6	10	2.4	3	3.5
MGFC42V3436	41.5	42.5	-	12	-42	-45	37	3.4~3.6	10	4.5	-	1.9
MGFC44V3436	43	44	-	11	-42	-45	36	3.4~3.6	10	6.4	-	1.2
MGFC45V3436A	44	45	-	10	-42	-45	36	3.4~3.6	10	8	0.8	1
MGFL45V1920A	44	45	-	12	-42	-45	45	1.9~2.0	10	6.5	-	1.5
MGFL48V1920	-	-	47	10	-	-	45	1.9~2.0	12	4	1	1.4
MGFS44V2735	43	44	-	11	-42	-45	36	2.7~3.5	10	6.4	1	1.2
MGFS45A2527B	44	45	-	11	-42	-45	40	2.5~2.7	10	6.5	-	1.4
MGFS45V2123A	44	45	-	11	-42	-45	45	2.1~2.3	10	6.5	-	1.5
MGFS45V2325A	44	45	-	11	-42	-45	45	2.3~2.5	10	6.5	-	1.5
MGFS45V2527A	44	45	-	11	-42	-45	45	2.5~2.7	10	6.5	-	1.5
MGFS45V2735	44	45	-	11	-42	-45	36	2.7~3.5	10	8	0.8	1
MGFS48B2122	-	-	47	11	-	-	48	2.11~2.17	12	2	1	1.2
MGFS48V2527	-	-	47	9	-	-	45	2.5~2.7	12	4	1	1.4
MGFS52BN2122A*	-	-	50.8	11	-	-	48	2.17	12	4	0.55	0.8

* : Communication grade
Ta=25°C

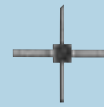
* : New product



GD-4



GD-9



GD-11



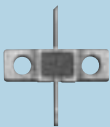
GD-16



GD-24



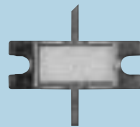
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GD-27



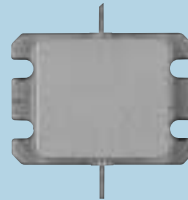
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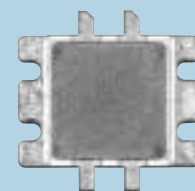
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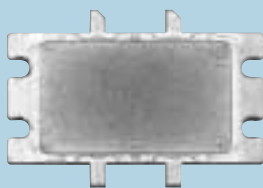
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GF-38



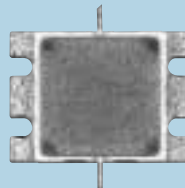
GF-47



GF-49



GF-50



GF-51



GF-55

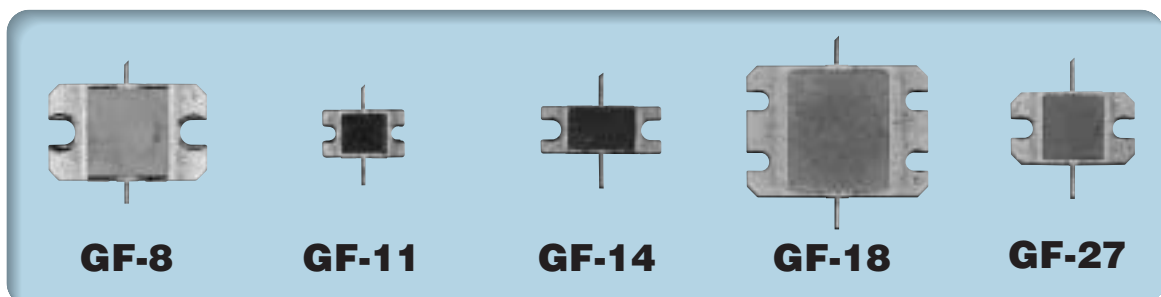
INTERNALLY MATCHED GaAs FET SERIES FOR C BAND HIGH POWER AMPLIFIERS

PRODUCT LIST

Type Number	Output Power at 1dB Gain Compression(dBm)		Linear Power Gain(dB)	3rd Order IM Distortion(dBc)		Power Added Efficiency(%)	Frequency (GHz)	Drain-Source Voltage(V)	Drain Current (A)	Thermal Resistance (°C/W)	
	Min.	Typ.		Min.	Typ.					Typ.	Max.
MGFC36V3742A	35	37	10	-42	-45	33	3.7~4.2	10	1.2	5	6
MGFC36V4450A	35	37	9	-42	-45	32	4.4~5.0	10	1.2	5	6
MGFC36V5258	35	36	9	-	-	33	5.2~5.8	10	1.2	-	6
MGFC36V5867	35	36	8.5	-	-	30	5.8~6.75	10	1.2	5	6
MGFC36V5964A	35	37	9	-42	-45	30	5.9~6.4	10	1.2	5	6
MGFC36V6472A	35	37	8	-42	-45	30	6.4~7.2	10	1.2	5	6
MGFC36V7177A	35	36.5	8	-42	-45	30	7.1~7.7	10	1.2	5	6
MGFC36V7785A	35	36.5	7	-42	-45	29	7.7~8.5	10	1.2	5	6
MGFC38V5867	37	38	8	-	-	32	5.8~6.75	10	1.8	-	5
MGFC38V5964	37	38	9	-42	-45	32	5.9~6.4	10	1.8	-	5
MGFC38V6472	37	38	8	-42	-45	31	6.4~7.2	10	1.8	-	5
MGFC39V3742A	38	39.5	9	-42	-45	31	3.7~4.2	10	2.4	-	3.5
MGFC39V4450A	38	39	8	-42	-45	30	4.4~5.0	10	2.4	-	3.5
MGFC39V5258	38	39	8	-	-	30	5.2~5.8	10	2.4	-	3.5
MGFC39V5867	38	39	8	-	-	30	5.8~6.75	10	2.4	-	3.5
MGFC39V5964A	38	39.5	8	-42	-45	30	5.9~6.4	10	2.4	-	3.5
MGFC39V6472A	38	39.5	7	-42	-45	28	6.4~7.2	10	2.4	-	3.5
MGFC39V7177A	38	39.5	7	-42	-45	28	7.1~7.7	10	2.4	-	3.5
MGFC39V7785A	38	39.5	6	-42	-45	27	7.7~8.5	10	2.4	-	3.5
MGFC40V3742	39.5	40.5	9	-42	-45	32	3.7~4.2	10	2.4	-	3.5
MGFC40V4450	39.5	40.5	9	-42	-45	32	4.4~5.0	10	2.4	-	3.5
MGFC40V5258	39.5	40.5	8	-	-	32	5.2~5.8	10	2.4	-	3.5
MGFC40V5964	39.5	40.5	8	-42	-49	30	5.9~6.4	10	2.4	3	3.5
MGFC40V6472	39.5	40.5	7	-42	-45	32	6.4~7.2	10	2.4	-	3.5
MGFC40V7177	39	40	7	-42	-45	32	7.1~7.7	10	2.4	-	3.5
MGFC40V7785	39	40	6	-42	-45	32	7.7~8.5	10	2.4	-	3.5
MGFC41V3642	40	41.5	11	-42	-45	40	3.6~4.2	10	3.4	-	2.8
MGFC41V5964	40	41	8.5	-42	-45	33	5.9~6.4	10	3.4	-	2.8
MGFC41V6472	40	41	8	-42	-45	32	6.4~7.2	10	3.4	2.2	2.8
MGFC41V7177	39.5	41	7	-42	-45	29	7.1~7.7	10	3.4	-	2.8
MGFC42V3742	41.5	42.5	9	-42	-45	32	3.7~4.2	10	4.5	-	1.9
MGFC42V4450	41.5	42.5	9	-42	-45	32	4.4~5.0	10	4.5	-	1.9
MGFC42V5258	41.5	42.5	8	-	-	31	5.2~5.8	10	4.5	-	1.9
MGFC42V5867	41	42.5	7	-	-	31	5.8~6.75	10	4.5	-	1.9
MGFC42V5964	41.5	42.5	8	-42	-45	31	5.9~6.4	10	4.5	1.6	1.9
MGFC42V5964A	41.5	42.5	8	-42	-45	33	5.9~6.4	10	4.5	-	1.6
MGFC42V6472	41.5	42.5	7	-42	-45	30	6.4~7.2	10	4.5	-	1.9
MGFC42V6472A	41.5	42.5	7	-42	-45	31	6.4~7.2	10	4.5	-	1.6
MGFC42V7785A	41	42	6	-42	-45	28	7.7~8.5	10	4.5	-	1.6
MGFC44V3642	43	44	10	-42	-45	35	3.6~4.2	10	6.4	-	1.6
MGFC44V4450	43	44	10	-42	-45	35	4.4~5.0	10	6.4	-	1.6
MGFC44V5964	43	44	8	-42	-	33	5.9~6.4	10	6.4	-	1.6
MGFC44V6472	43	44	7	-42	-	31	6.4~7.2	10	6.4	-	1.6
MGFC45V3642A	44	45	10	-42	-45	36	3.6~4.2	10	8	0.8	1
MGFC45V4450A	44	45	9	-42	-45	34	4.4~5.0	10	8	0.8	1
MGFC45V5867	43.5	45	7	-	-	35	5.8~6.75	10	8	-	1
MGFC45V5964A	44	45	8	-42	-45	33	5.9~6.4	10	8	0.8	1
MGFC45V6472A	44.5	45	7	-42	-45	35	6.4~7.2	10	8	-	1
MGFC47V5864	46	47	8.5	-	-	35	5.8~6.4	10	9.8	0.8	0.9
MGFC47A4450	46	47	9.5	-	-	40	4.4~5.0	10	9.8	0.8	0.9
MGFC48B5864**	47	48	8	-	-	35	5.8~6.4	10	14	0.65	0.75

Ta=25°C

** : Under development



INTERNALLY MATCHED GaAs FET SERIES FOR X/Ku BAND HIGH POWER AMPLIFIERS

Type Number	Output Power at 1dB Gain Compression(dBm)		Linear Power Gain(dB)	3rd Order IM Distortion(dBc)		Power Added Efficiency(%)	Frequency (GHz)	Drain-Source Voltage(V)	Drain Current (A)	Thermal Resistance (°C/W)	
	Min.	Typ.		Min.	Typ.					Typ.	Max.
	MGFK25V4045	24	25	7	-	-	25	14~14.5	8	0.15	-
MGFK30V4045	29	30	7	-	-	24	14~14.5	8	0.35	-	29
MGFK33V4045	32	33	5.5	-	-	22	14~14.5	8	0.7	-	10
MGFK35V4045	34.5	35.4	5.5	-	-	20	14~14.5	10	1.2	-	4.5
MGFK37V4045	36.5	37.4	4.5	-	-	17	14~14.5	10	2.4	-	3.5
MGFK39V4045	38.5	39	4.5	-	-	20	14~14.5	10	2.4	-	3.5
MGFK38A3745**	37	38	7	-	-	30	13.75~14.5	10	1.5	3.6	4
MGFK41A4045*	40	41	6	-	-	25	14.0~14.5	10	3	1.8	2.2
MGFK44A4045*	43	44	5	-	-	17	14.0~14.5	10	6	1	1.3
MGFX35V0510*	34.5	35.5	7	-	-	30	10.5~11.0	10	1.2	-	5.5
MGFX36V0717	34.5	36	7	-	-	32	10.7~11.7	10	1.2	-	5.5
MGFX38V0510*	37	38	6	-	-	26	10.5~11.0	10	2.4	-	3.5
MGFX39V0717	37.5	39	6	-	-	36	10.7~11.7	10	2.4	-	3.5

* : Communication grade
Ta=25°C

* : New product ** : Under development

GaAs HYBRID IC

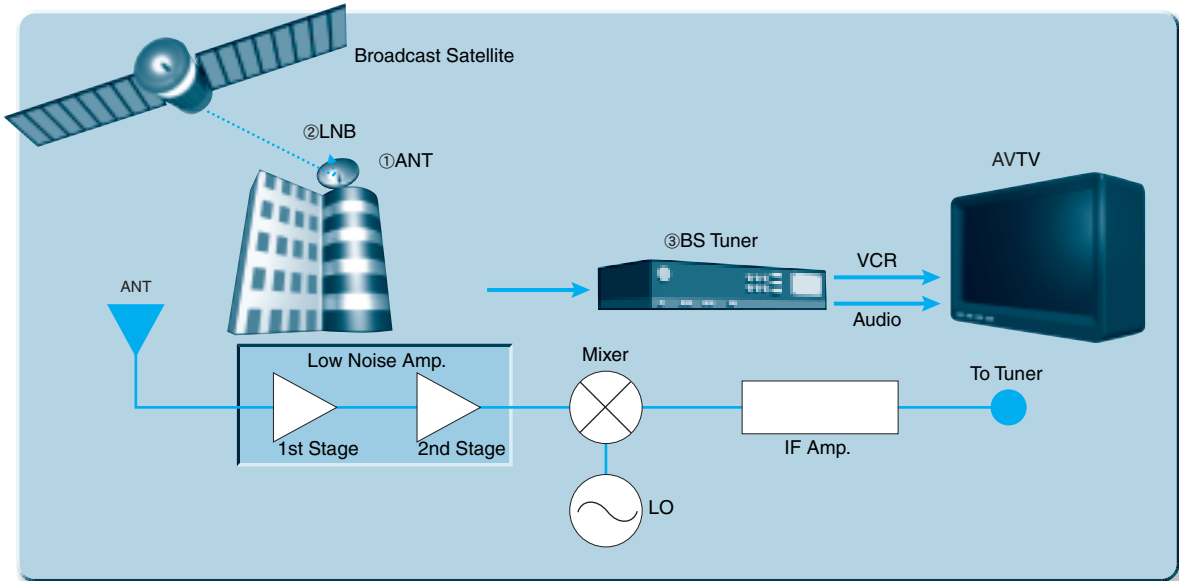
Type Number	Application	fL(MHz)	fH(MHz)	Po(dBm)	VD(V)	VG(V)	Eff(%)	Pin(dBm)	Package outline
FA01252	PDC800	893	958	30.6	3.6	-2.3	-	4.0	GH-40
		940	958	30.6	3.6	-2.3	60	4.5	
FA01249	PDC1.5G	1439	1468	29.8	3.6	-2.3	60	5.0	GH-38
FA01251	PDC1.5G	1429	1453	31.0	3.5	-2.5	60	6.0	GH-38
FA01253*	PDC1.5G(※1)	1429	1453	29.8	3.5	-2.5	60	5.0	GH-40
BA01207	N-CDMA(JAPAN)	887	925	27.5	3.5	2.8	41	0	GH-34
BA01222	N-CDMA(USA)/AMPS	824	849	27.5	3.5	3.0	38	0	GH-36
BA01231*	W-CDMA	830	840	26.5	3.5	2.9	45	-1.0	GH-39
BA01232*	W-CDMA	1920	1980	26.5	3.5	2.9	50	-1.0	GH-39
BA01202	N-CDMA(USA)	1850	1910	28.0	3.2	3.0	38	3.0	GH-30

※1 : It's available to change the frequency range(fL=1439MHz, fH=1468MHz).

* : New product

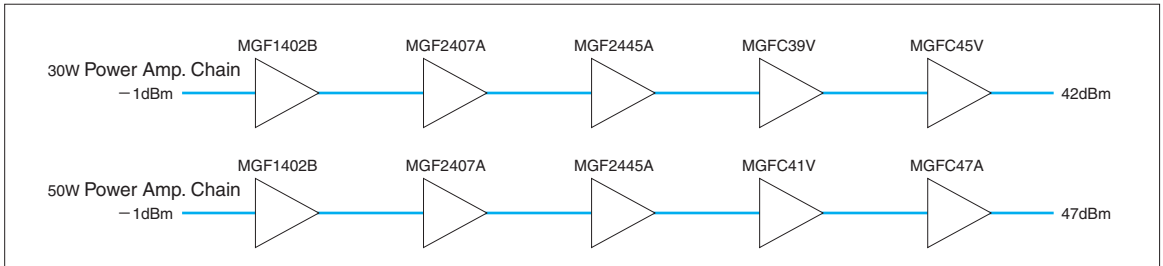
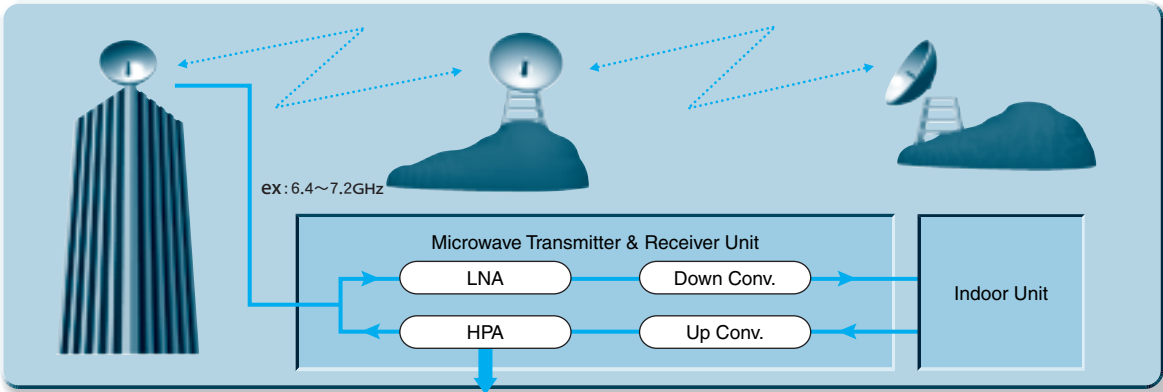
Type Number	Application	fL(MHz)	fH(MHz)	Po(dBm)	Pin(dBm)	Vc(V)	It(mA)	Vpc(V)	Ipc(mA)	Remarks	Package outline
BA01303	GSM900/DCS1800/PCS1900	880	915	33.0	3.0	3.5	1350	<2.6	5.5	Triple-band	GH-32

Lineup for 12GHz -Band LNB

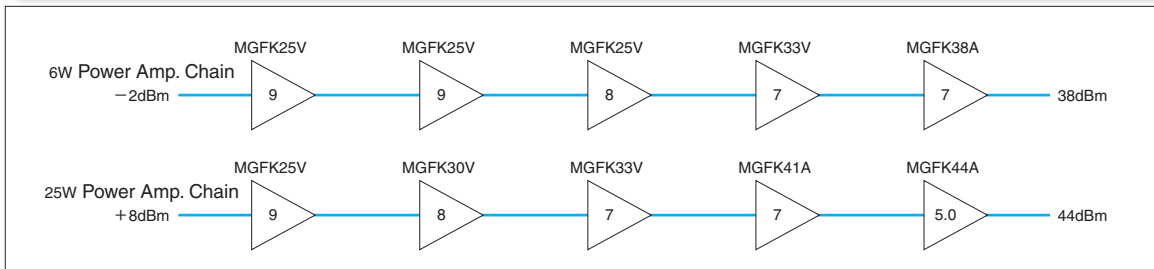
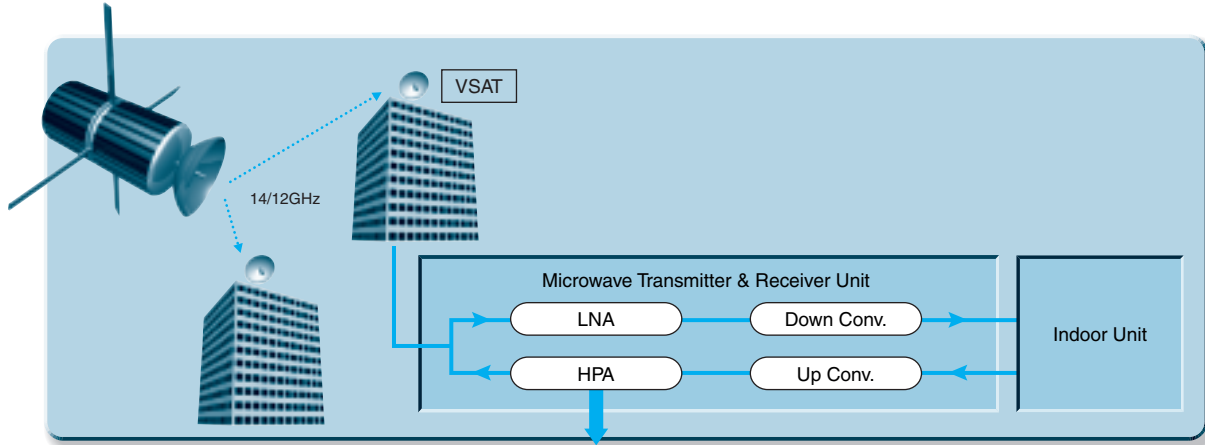


Noise Performance of LNB	1st Stage	2nd Stage	Mixer
0.8-1.0dB	MGF4953A	MGF4954A	MGF4954A
0.9-1.1dB	MGF4954A	MGF4954A	MGF4954A

Lineup for Microwave Links



Lineup for Satellite Communication



Application Note

Contents	Date
Recommended assemble method for MITSUBISHI's leadless package HEMT	Sep./2002